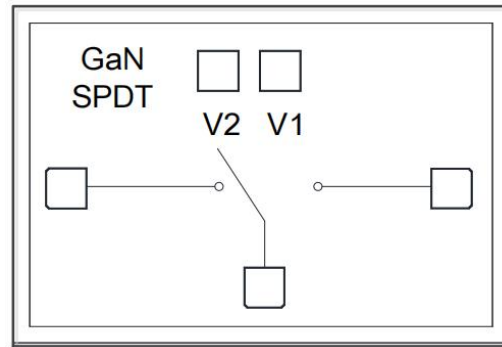


Performance

- Frequency: 5~7GHz
- Insertion loss: 0.7dB
- Isolation: 35dB
- Input P-0.3: 49dBm
- Input/Output VSWR: 1.3:1
- Switching Time: 20ns
- Control Mode: 0/-40V
- Voltage control reflective switch
- Chip size: 2.7*3.0*0.08mm

Function Diagram



Electrical Specifications (Ta=+25°C, V1~V2=0V/-40V, F=5~7GHz)

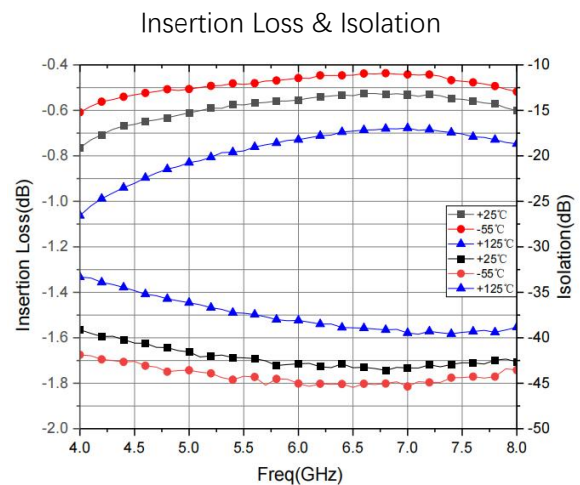
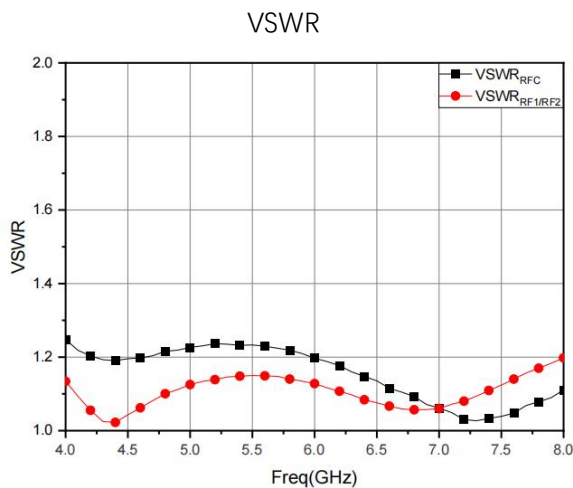
Symbol	Parameter	Min.	Typ.	Max.	Unit
Li	Insertion Loss	-	0.7	-	dB
ISO	Isolation	-	35	-	dB
VSWR	Input / Output VSWR	-	1.3	-	-

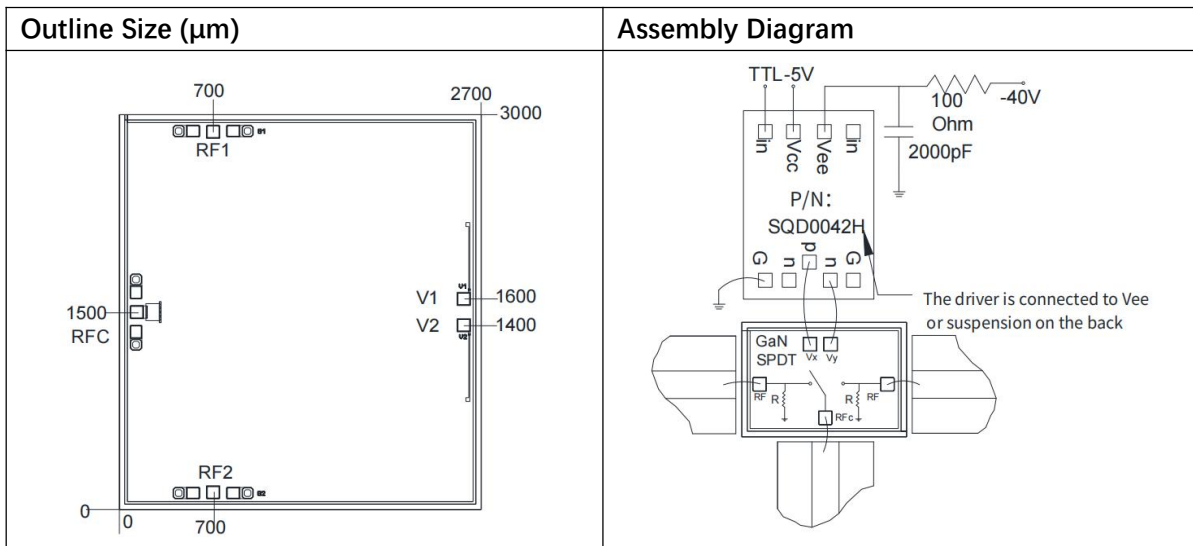
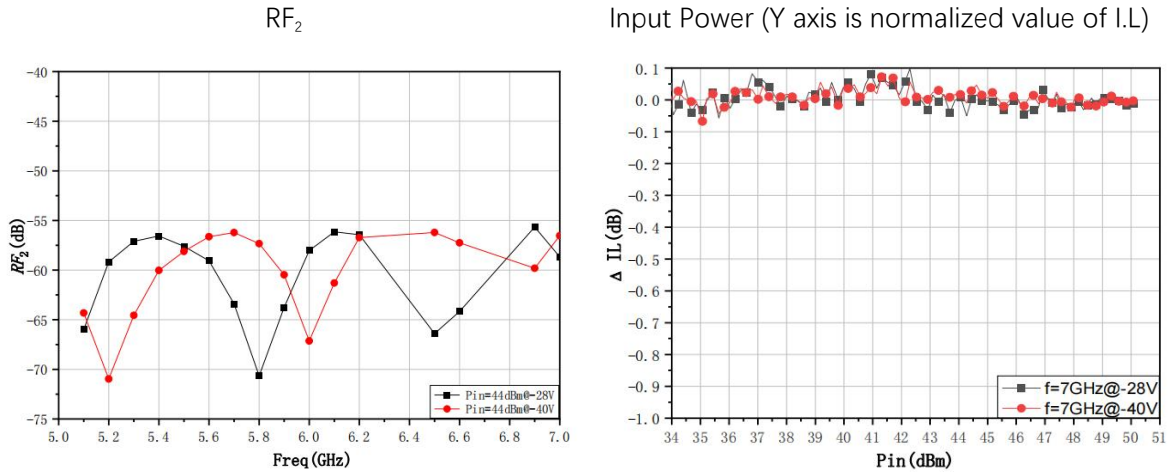
Absolute Maximum Ratings (Ta=+25°C)

Symbol	Parameter	Value	Notes
V1,2	Control Voltage	-60V	
Pcw	Input Continuous Wave Power	50dBm	
Tch	Channel Temperature	225°C	
T	Sintering Temperature	310°C	30s, N2 protection
Tstg	Storage Temperature	-65~150°C	

Exceed any of above listed ratings may cause permanent damage.

Test Curves (Ta=+25°C, (V1,2=-40V))





- Note: 1, For same pads, choose any of them.
2, RF input/output dual wire length is less than 300 μm .

PIN Definition

PIN	Description
RF1、RF2	RF ports, 50 Ω , no block capacitor
RFc	RF common ports, 50 Ω , block capacitor
V1、V2	Control Ports
GND	Bottom must be grounded

Truth Table

V1	V2	$RF_c \rightarrow RF_1$	$RF_c \rightarrow RF_2$
0	1	ON	OFF
1	0	OFF	ON

- Note: 1. Low level "0" is -28V~-40V, High level "1" is 0V~0.5V
2. Performance is same under condition of -28V ~ -40V

Note

- a) Use 80/20 gold tin for sintering, the sintering temperature should not exceed 300°C, and the sintering time should be as short as possible, not exceeding 30 seconds;
- b) The chip is an electrostatic sensitive device, and anti-static should be paid attention to during use, transportation and operation;
- c) Two bonding wires (gold wires with a diameter of 25 μm) are used for input and output, and the length of the bonding wire is about 300 μm is the best;
- d) This product is a hydrogen sensitive device with a hydrogen resistance of 20000ppm. It is recommended to control the hydrogen concentration in the sealed cavity when using it.